Si $V_{in}=V_{out}=V_M$, aleshores els dos transistors estàn en saturació. Per tant:

$$\left.\begin{aligned} I_{DS}(\text{NMOS}) &= \frac{\beta_n}{2}\left(V_{GS}-V_{Tn}\right)^2 \\ I_{SD}(\text{PMOS}) &= \frac{\beta_p}{2}\left(V_{SG}-\left|V_{Tp}\right|\right)^2 \end{aligned}\right\}$$

A més, $I_{DS}=I_{SD}$

Per tant:

$$\frac{\beta_n}{2}\left(V_{GS}-V_{Tn}\right)^2 = \frac{\beta_p}{2}\left(V_{SG}-\left|V_{Tp}\right|\right)^2$$

És a dir:

$$\frac{\beta_n}{\beta_p} = \frac{\left(V_{SG}-\left|V_{Tp}\right|\right)^2}{\left(V_{GS}-V_{Tn}\right)^2} = \frac{\left(V_{DD}-V_M-\left|V_{Tp}\right|\right)^2}{\left(V_M-V_{Tn}\right)^2}$$

I, com $\beta=(W/L)\cdot\mu\cdot C_{ox}=K\cdot\mu\cdot C_{ox}$

$$\frac{(W/L)_n}{(W/L)_p} = \frac{K_n}{K_p} = \frac{\mu_p}{\mu_n}\frac{\left(V_{DD}-V_M-\left|V_{Tp}\right|\right)^2}{\left(V_M-V_{Tn}\right)^2}$$

I les dades que necessitau, del model de 0.25μm, són:

V_{Tp}= -0.65V
V_{Tn}= 0.65V
μ_n= 130 cm^2/s
μ_p= 100 cm^2/s